

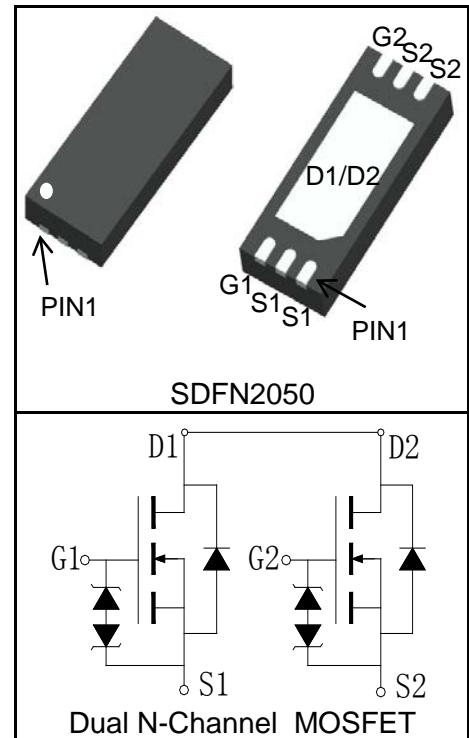
Features

- 20V/8A,
 $R_{DS(ON)} = 13m\Omega(Typ.)@V_{GS}=4.5V$
 $R_{DS(ON)} = 14m\Omega(Typ.)@V_{GS}=4V$
 $R_{DS(ON)} = 16m\Omega(Typ.)@V_{GS}=3.1V$
 $R_{DS(ON)} = 18m\Omega(Typ.)@V_{GS}=2.5V$
- Super High Dense Cell Design
- Fast Switching Speed
- ESD Protected
- 100% avalanche tested
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- DC-DC Converters
- Power Management

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit	
Common Ratings ($T_C=25^\circ C$ Unless Otherwise Noted)				
V_{DSS}	Drain-Source Voltage	20	V	
V_{GSS}	Gate-Source Voltage	± 10		
T_J	Maximum Junction Temperature	150	$^\circ C$	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$	
I_S	Diode Continuous Forward Current	$T_C=25^\circ C$	28	A
Mounted on Large Heat Sink				
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_C=25^\circ C$	60	A
$I_D^{②}$	Continuous Drain Current@ $T_C(V_{GS}=4.5V)$	$T_C=25^\circ C$	28	A
		$T_C=100^\circ C$	18	
	Continuous Drain Current@ $T_A(V_{GS}=4.5V)^{③}$	$T_A=25^\circ C$	8	
		$T_A=70^\circ C$	6.4	
P_D	Maximum Power Dissipation@ T_C	$T_C=25^\circ C$	25	W
		$T_C=100^\circ C$	10	
	Maximum Power Dissipation@ $T_A^{③}$	$T_A=25^\circ C$	1.7	
		$T_A=70^\circ C$	1.1	

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	5	°C/W
$R_{\theta JA}^{(3)}$	Thermal Resistance-Junction to Ambient	75	°C/W
Drain-Source Avalanche Ratings			
$E_{AS}^{(4)}$	Avalanche Energy, Single Pulsed	TBD	mJ

Electrical Characteristics ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

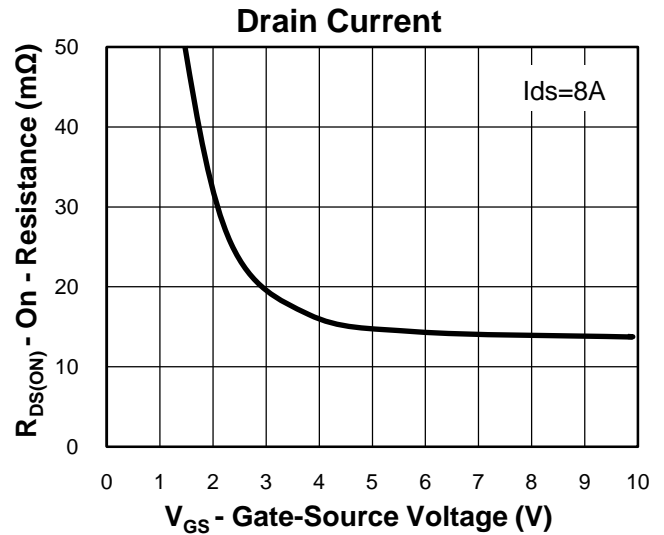
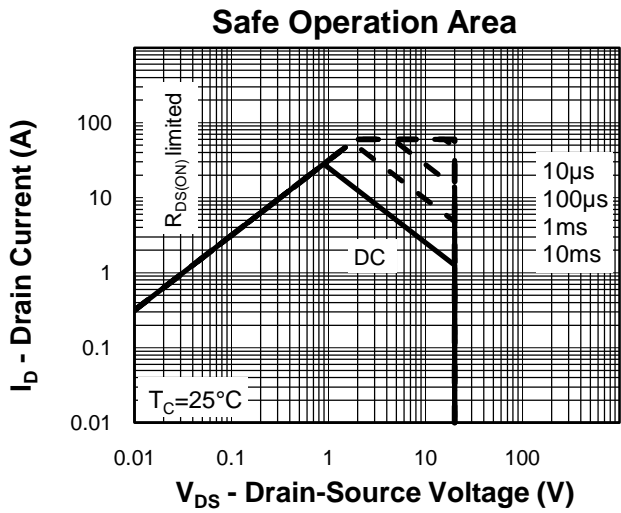
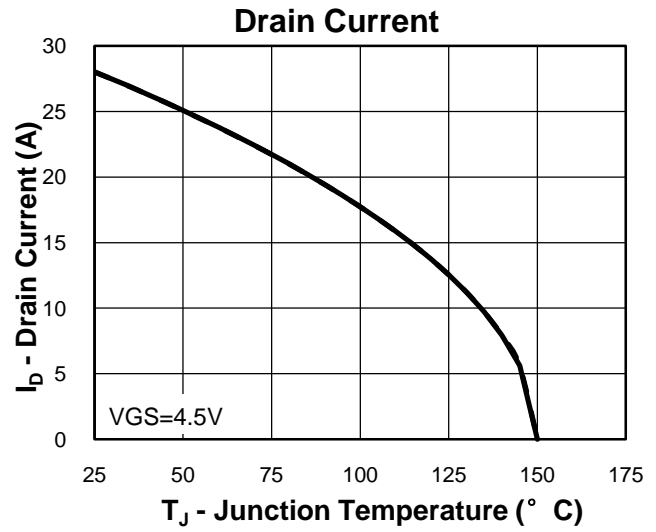
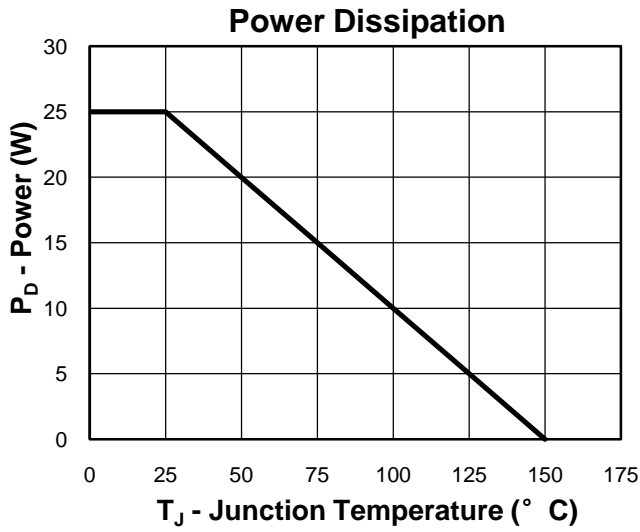
Symbol	Parameter	Test Condition	RU20T8M7			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	20	24		V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V$			1	μA
		$T_J=125^\circ C$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	0.5		1.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 10V, V_{DS}=0V$			± 10	μA
$R_{DS(ON)}^{(5)}$	Drain-Source On-state Resistance	$V_{GS}=4.5V, I_{DS}=8A$		13	15	$m\Omega$
		$V_{GS}=4V, I_{DS}=7A$		14	16	$m\Omega$
		$V_{GS}=3.1V, I_{DS}=6A$		16	18	$m\Omega$
		$V_{GS}=2.5V, I_{DS}=5A$		18	20	$m\Omega$
Diode Characteristics						
$V_{SD}^{(5)}$	Diode Forward Voltage	$I_{SD}=8A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=8A, di_{SD}/dt=100A/\mu s$		25		ns
Q_{rr}	Reverse Recovery Charge			13		nC
Dynamic Characteristics⁽⁶⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		1.5		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=10V, \text{Frequency}=1.0MHz$		1150		pF
C_{oss}	Output Capacitance			180		
C_{riss}	Reverse Transfer Capacitance			140		
$t_{d(ON)}$	Turn-on Delay Time			5		
t_r	Turn-on Rise Time	$V_{DD}=10V, I_{DS}=8A, V_{GEN}=4.5V, R_G=2.5\Omega$		13		
$t_{d(OFF)}$	Turn-off Delay Time			34		
t_f	Turn-off Fall Time			17		
Gate Charge Characteristics⁽⁶⁾						
Q_g	Total Gate Charge	$V_{DS}=16V, V_{GS}=4.5V, I_{DS}=8A$		13		nC
Q_{gs}	Gate-Source Charge			1.2		
Q_{gd}	Gate-Drain Charge			3.9		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$.
 - ④ Limited by $T_{J\text{max}}$, $V_{DD} = 16\text{V}$, $R_G = 50\Omega$, Starting $T_J = 25^\circ\text{C}$.
 - ⑤ Pulse test; Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

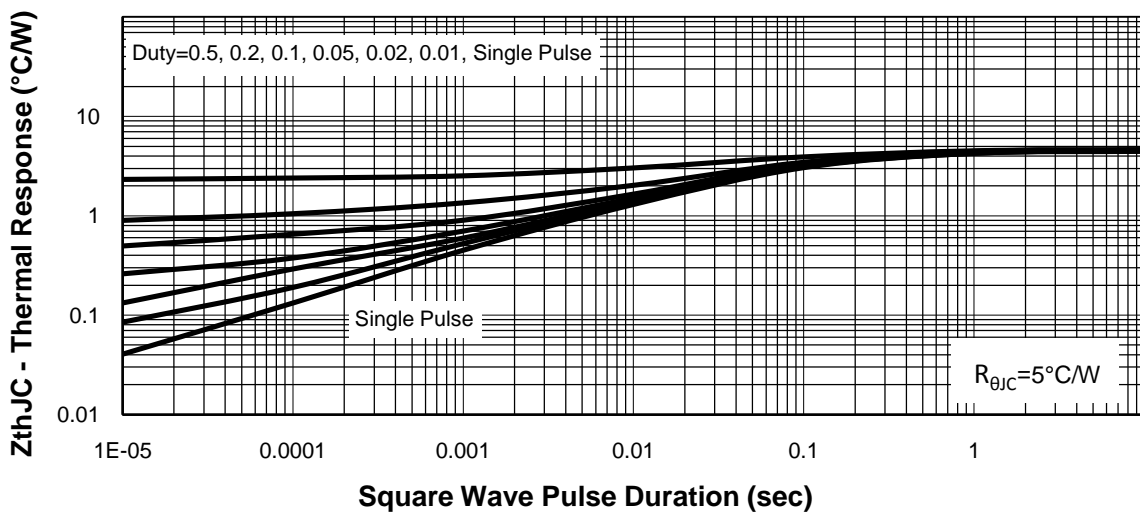
Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU20T8M7	RU20T8M7	SDFN2050	Tape&Reel	2500	7"	12mm

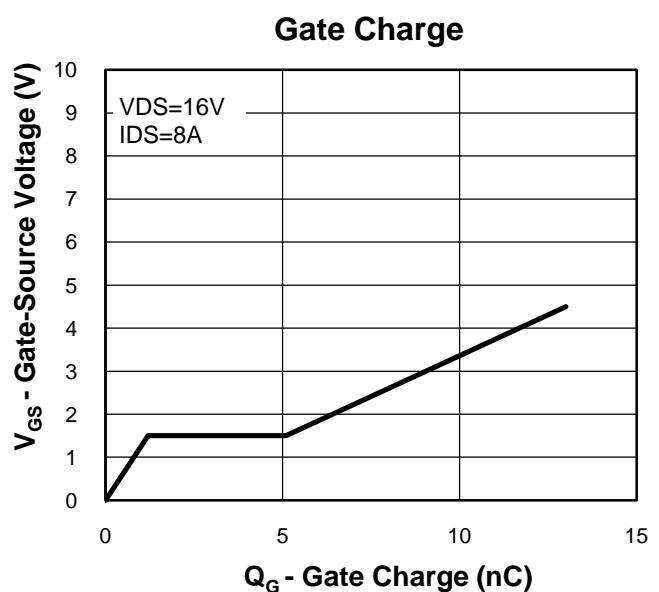
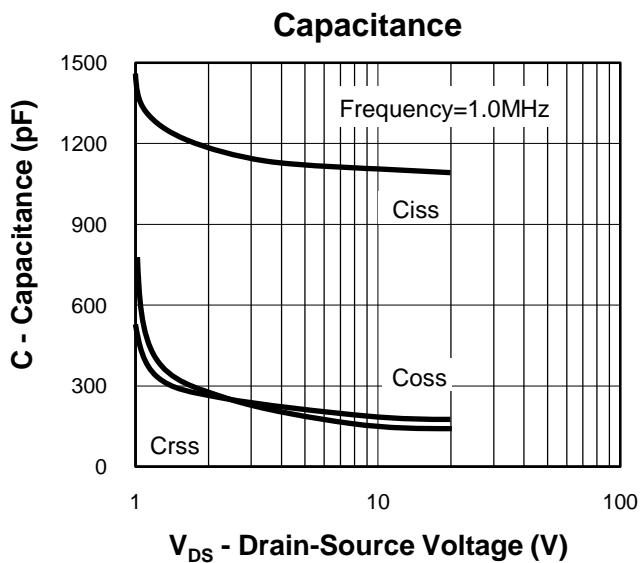
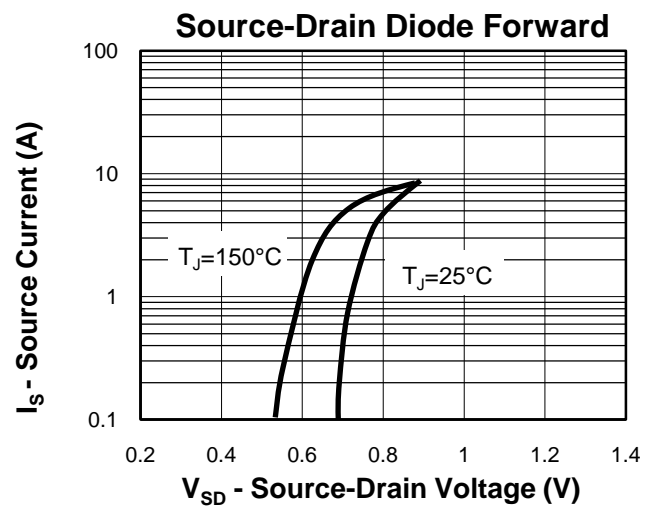
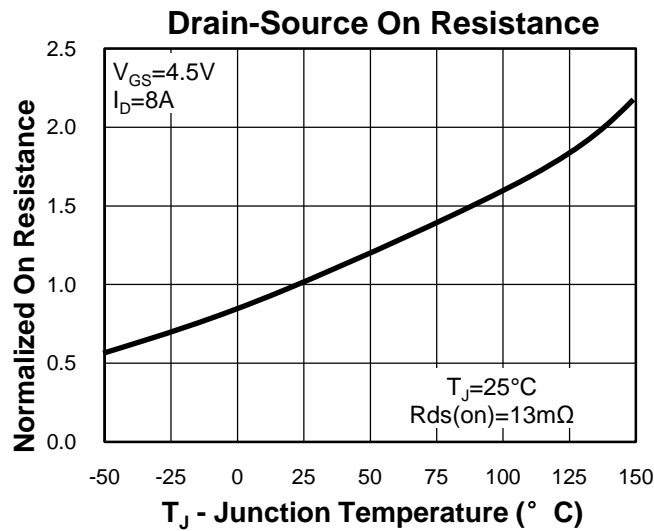
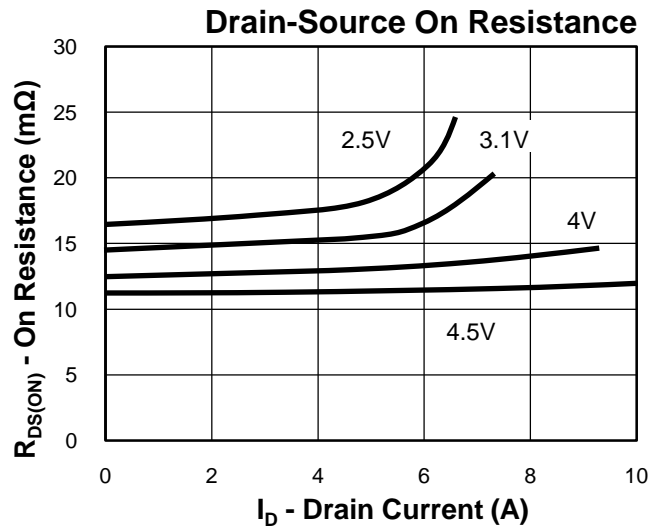
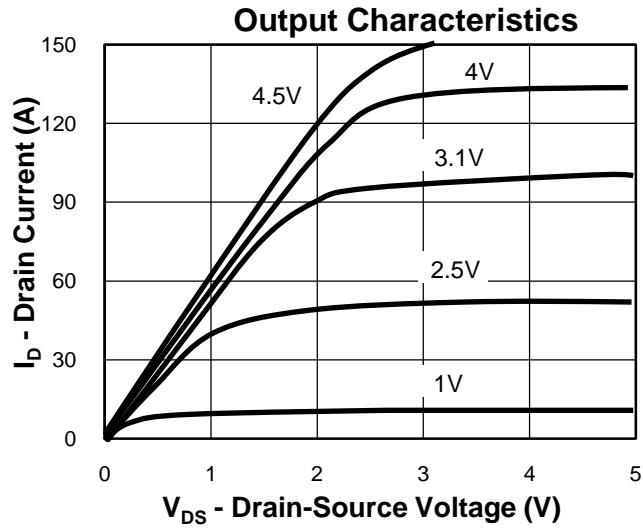
Typical Characteristics



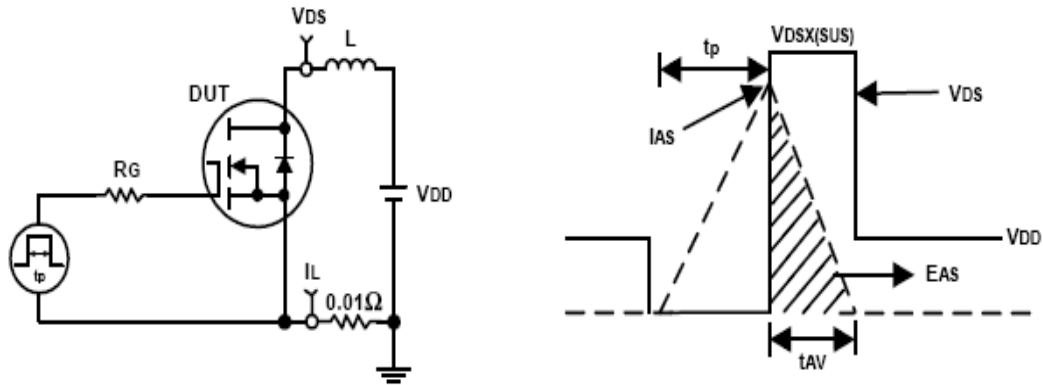
Thermal Transient Impedance



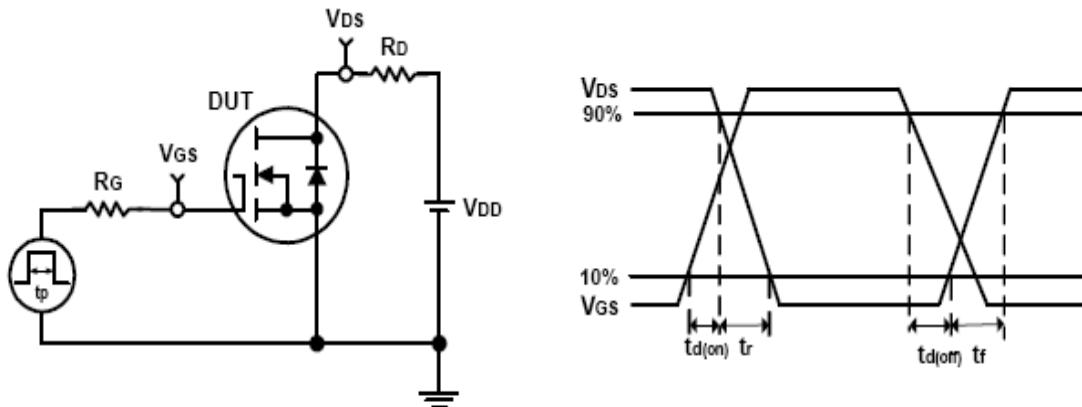
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Avalanche Test Circuit and Waveforms

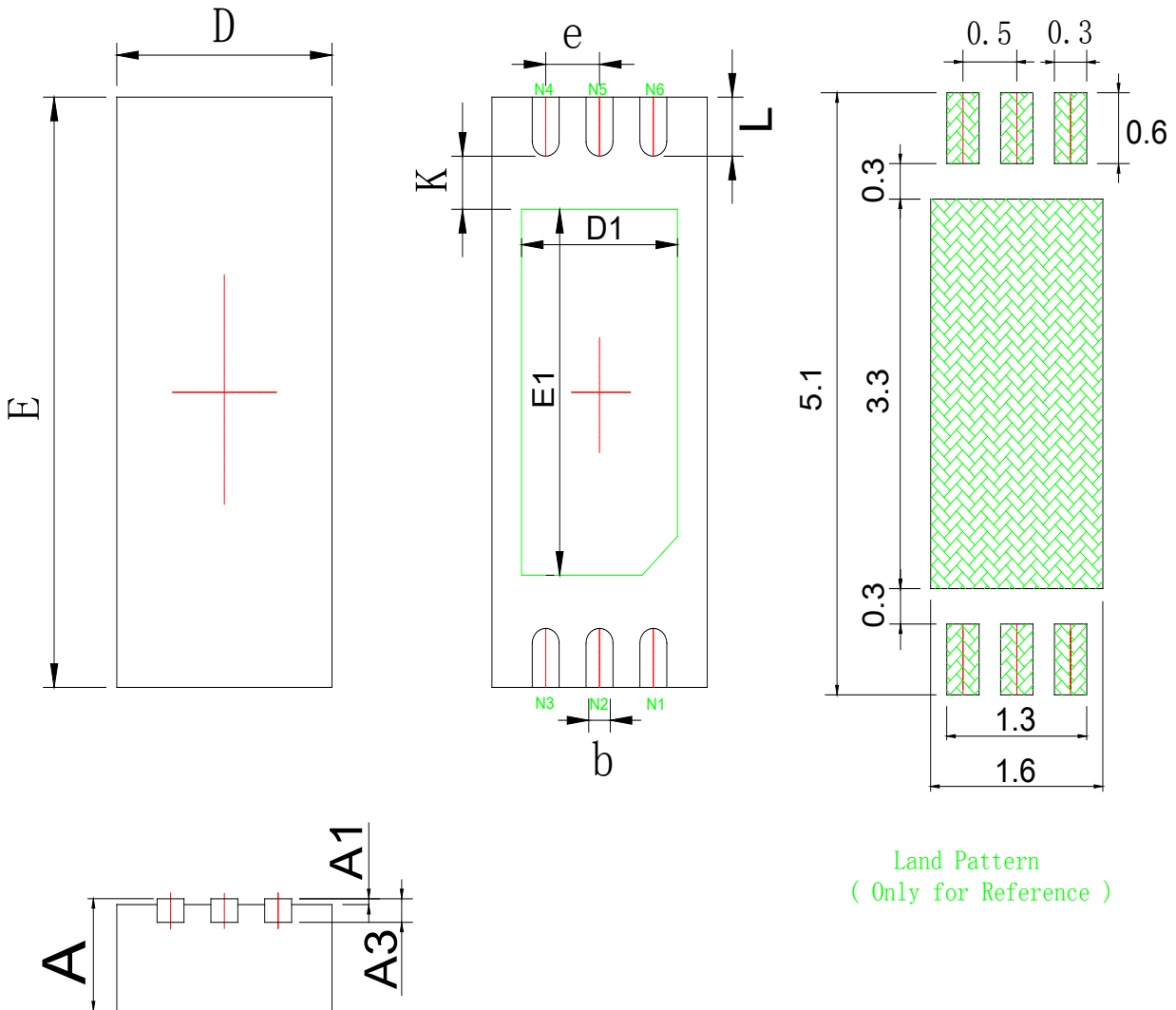


Switching Time Test Circuit and Waveforms



Package Information

SDFN2050



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.800	0.900	0.028	0.031	0.035
A1	0.000	0.025	0.050	0.000	0.001	0.002
A3	0.203 REF.			0.008 REF.		
D	1.924	2.000	2.076	0.076	0.079	0.082
E	4.924	5.000	5.076	0.194	0.197	0.200
D1	1.350	1.450	1.550	0.053	0.057	0.061
E1	2.950	3.050	3.150	0.116	0.120	0.124
K	0.200 MIN.			0.008 MIN.		
b	0.200	0.250	0.300	0.008	0.010	0.012
e	0.500 TYP			0.020 TYP		
L	0.424	0.500	0.576	0.017	0.020	0.023

Customer Service

Worldwide Sales and Service:

Sales@ruichips.com

Technical Support:

Technical@ruichips.com

Investor Relations Contacts:

Investor@ruichips.com

Marcom Contact:

Marcom@ruichips.com

Editorial Contact:

Editorial@ruichips.com

HR Contact:

HR@ruichips.com

Legal Contact:

Legal@ruichips.com

Shen Zhen RUICHIPS Semiconductor CO., LTD

Room 501, the 5floor An Tong Industrial Building,
NO.207 Mei Hua Road Fu Tian Area Shen Zhen City, CHINA

TEL: (86-755) 8311-5334

FAX: (86-755) 8311-4278

E-mail: Sales-SZ@ruichips.com